

Contents

Acknowledgements	v
Resumen - Resum - Abstract	vii
List of tables	xvii
List of figures	xix
List of acronyms	xxv
1 Introduction	1
1.1 Silicon-based integrated photonics	1
1.1.1 Silicon technology	2
1.1.2 Applications	3
1.1.3 Beyond silicon: Hybrid material integration	12
1.2 Metal oxides for hybrid integrated photonics	15
1.2.1 Transparent conducting oxides (TCOs)	15
1.2.2 Vanadium dioxide (VO_2)	21
1.3 Objectives, methodology, and outline of the thesis	26
2 Toward non-volatile switching in silicon photonic devices	31
2.1 Review of non-volatile technologies for silicon photonics	32
2.1.1 Introduction	32
2.1.2 Optical bistability on silicon	35

2.1.3	Non-volatile switching enabled by device engineering	37
2.1.4	Non-volatile switching enabled by materials integration	47
2.1.5	Conclusions and perspectives	58
2.2	Non-volatile epsilon-near-zero readout memory	62
2.2.1	Memory architecture and working principle	62
2.2.2	Selection of the tunneling and blocking oxides	63
2.2.3	Electrical modeling and retention time	64
2.2.4	Writing/erasing power consumption and speed	66
2.2.5	Optical performance	68
2.3	Ultra-compact non-volatile Mach-Zehnder switch enabled by a high-mobility TCO	71
2.3.1	Non-volatile Mach-Zehnder switch concept	71
2.3.2	CdO as an alternative to ITO for low-loss phase-based applications	73
2.3.3	Optimal carrier concentration of CdO floating gate	73
2.3.4	Electro-optic performance	78
2.4	Discussion	80
3	Power-efficient thermo-optic phase shifters using TCO-based transparent heaters	83
3.1	Review of thermo-optic phase shifters in silicon	84
3.1.1	Introduction	84
3.1.2	Thermo-optic phase shifters: fundamentals and configurations	90
3.1.3	All-optical phase shifters	107
3.2	Ultra-low loss hybrid ITO/Si thermo-optic phase shifter with optimized power consumption	112
3.2.1	Design methodology	112
3.2.2	Influence of the spacer on the power consumption and switching speed	114
3.2.3	Experimental results	118
3.3	All-optical phase control in nanophotonic silicon waveguides with epsilon-near-zero nanoheaters	123
3.3.1	Working principle	124
3.3.2	Optimal ENZ layer: thickness and loss	124

3.3.3	Coupling loss and excitation of higher-order modes	125
3.3.4	Thermo-optic performance	127
3.3.5	Implementation with TCOs	129
3.4	Discussion	131
4	Ultra-compact and broadband nonlinear optical devices using VO₂	135
4.1	Review of nonlinear optical integrated devices	135
4.1.1	Introduction	136
4.1.2	Nonlinear integrated devices with functional materials . . .	138
4.1.3	Optically switched silicon devices using VO ₂	144
4.2	All-optical VO ₂ /Si waveguide absorption switch at telecom wavelengths	147
4.2.1	VO ₂ /Si waveguide and its transmission response	147
4.2.2	Experimental all-optical switching performance	150
4.3	Low-threshold power and tunable integrated optical limiter based on an ultra-compact VO ₂ /Si waveguide	156
4.3.1	In-plane photothermal response	156
4.3.2	Optical limiting condition	158
4.3.3	Experimental results	159
4.4	Discussion	164
5	Conclusions and future directions	167
Author's merits		175
A	Appendices	181
A.1	Simulations methods	181
A.1.1	Materials' properties	181
A.1.2	Optical simulations	182
A.1.3	Thermal simulations	183
A.2	Fabrication processes	188
A.3	Characterization setups	190
Bibliography		193